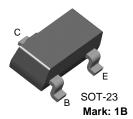


## **MMBT2222**

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### **NPN General Purpose Amplifier**

• Sourced from process 19.



# **Absolute Maximum Ratings\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	0.6	Α
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

<sup>\*</sup> This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### **Electrical Characteristics** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Off Characteristics						
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	30		V	
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	60		V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V	
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		10	μΑ	
		$V_{CB} = 50V, I_{E} = 0, T_{a} = 125^{\circ}C$		10	μΑ	
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$		10	nA	
On Charac	cteristics					
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1mA, V <sub>CE</sub> = 10V	35			
		$I_C = 1.0 \text{mA}, V_{CE} = 10 \text{V}$	50			
		$I_{C} = 10 \text{mA}, V_{CE} = 10 \text{V}$	75			
		$I_C = 150 \text{mA}, V_{CE} = 10 \text{V}^*$	100	300		
		$I_C = 150 \text{mA}, V_{CE} = 1.0 \text{V}^*$	50			
		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}^*$	30			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		0.4	V	
- (,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		1.6		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		1.3	V	
, ,		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		2.6		

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These rating are based on a maximum junction temperature of 150 degrees C.
 These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

<b>Electrical Characteristics</b>	(Continued) T <sub>a</sub> =25°C unless otherwise note	ed
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	Symbol	Parameter	Test Condition	Min.	Max.	Units
	Small Sign	nal Characteristics				
	f <sub>T</sub>	Curent Gain Bandwidth Product	$I_C = 20 \text{mA}, V_{CE} = 20 \text{V}, f = 100 \text{MHz}$	250		
	C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		8.0	pF
www.datasheet4	·u.com	Input Capacitance	$V_{EB} = 0.5V, I_{C} = 0, f = 1MHz$		30	pF
	Switching Characteristics					
	t <sub>d</sub>	Delay Time	$V_{CC} = 30V, V_{BE(OFF)} = 0.5V,$		10	ns
	t <sub>r</sub>	Rise Time	I <sub>C</sub> = 150mA, I <sub>B1</sub> = 15mA		25	ns
	t <sub>s</sub>	Storage Time	$V_{CC} = 30V, I_{C} = 150mA,$		225	ns
	t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 15mA$		60	ns

<sup>\*</sup> Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

# Thermal Characteristics $\rm T_a=25\,^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units	
P <sub>D</sub>	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	
+ D				

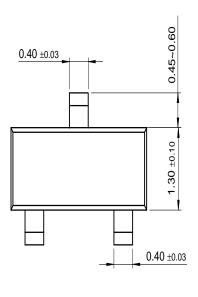
 $<sup>^{\</sup>star}$  Device mounted on FR-4PCB 1.6"  $\times$  1.6"  $\times$  0.06".

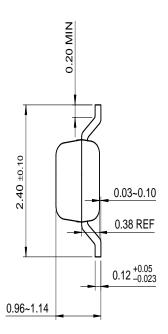
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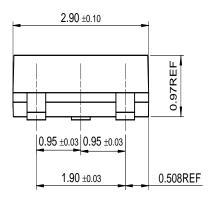
# **Package Dimensions**

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# SOT-23







Dimensions in Millimeters

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	DOME™	GTO™	MICROWIRE™	QT Optoelectronics™	TinyLogic <sup>®</sup>
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	E <sup>2</sup> CMOS™	I <sup>2</sup> C™	MSXPro™	RapidConfigure™	TruTranslation™
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	FACT Quiet Series <sup>T</sup>	M	OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
	Across the board. A	round the world.™	OPTOPLANAR™	SMART START™	
	The Power Franchise <sup>®</sup> Programmable Active Droop™		PACMAN™	SPM™	
			POP™	Stealth™	

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